

Features

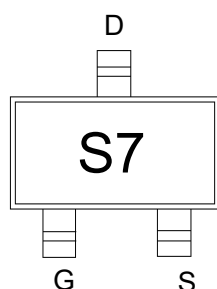
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-30V	88mΩ@-10V	-3.5A
	138mΩ@-4.5V	

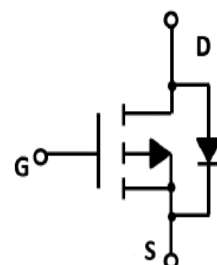
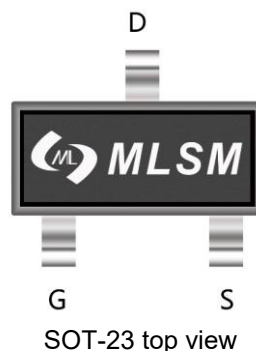
Application

- Battery protection
- Load switch
- Power management



S7: Device code

Marking and pin assignment



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C -1.5	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C -12	A
I_D	Continuous Drain Current	Tc=25°C -3.5	A
P_D	Maximum Power Dissipation	Tc=25°C 1.8	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	113	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
Si2307CDS	SOT-23	S7	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V, VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1	--	-3	V
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-3.5A	--	73	88	mΩ
		VGS=-4.5V, ID=-2.5A	--	110	138	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=-15V, VGS=0V, f=1MHz	--	340	--	pF
COSS	Output Capacitance		--	67	--	pF
CRSS	Reverse Transfer Capacitance		--	51	--	pF
Qg	Total Gate Charge	VDS=-15V, ID=-2.5A, VGS=-4.5V	--	4.1	--	nC
Qgs	Gate Source Charge		--	1.3	--	nC
Qgd	Gate Drain Charge		--	1.8	--	nC
Switching Characteristics						
td(on)	Turn-on Delay Time	VDS=-15V, ID=-1A, RL=15Ω, VGS=-4.5V, RG=1Ω	--	40	--	nS
tr	Turn-on Rise Time		--	40	--	nS
td(off)	Turn-Off Delay Time		--	20	--	nS
tf	Turn-Off Fall Time		--	17	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=-0.75A	--	-0.8	-1.2	V

Typical Operating Characteristics

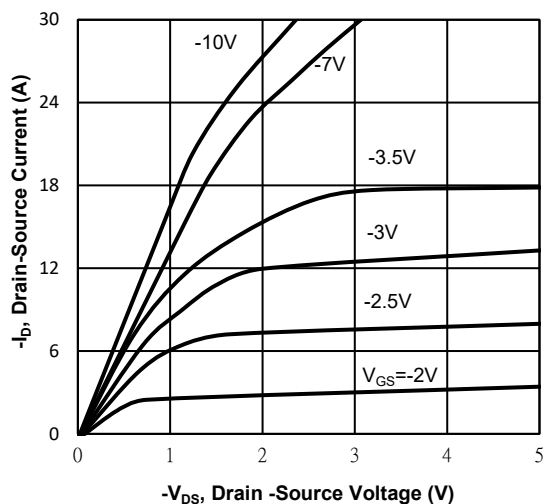


Fig1. Typical Output Characteristics

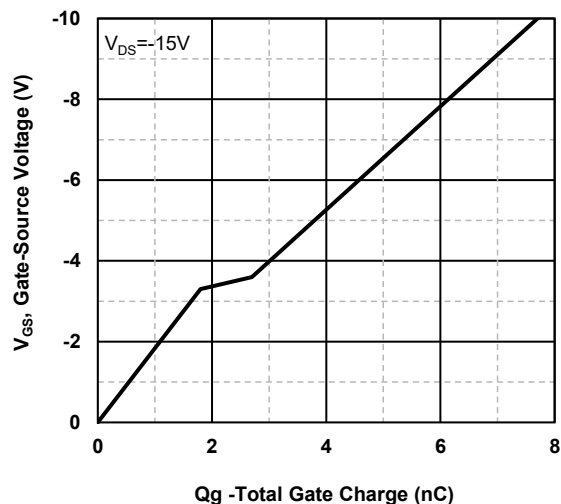


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

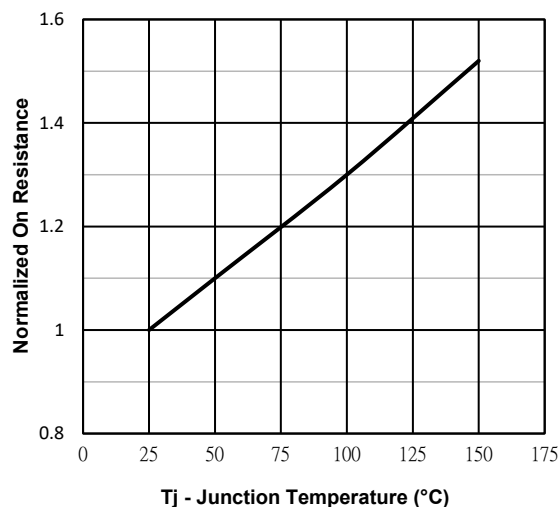


Fig3. Normalized On-Resistance Vs. Temperature

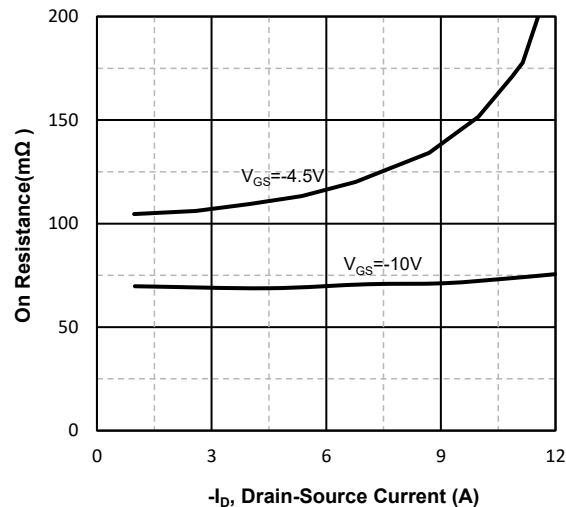


Fig4. On-Resistance Vs. Drain-Source Current

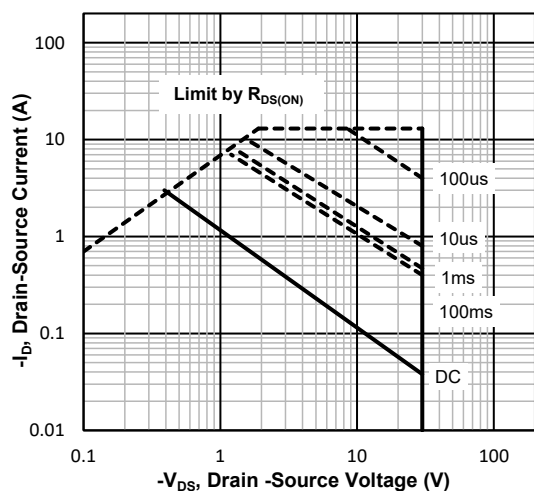


Fig5. Maximum Safe Operating Area

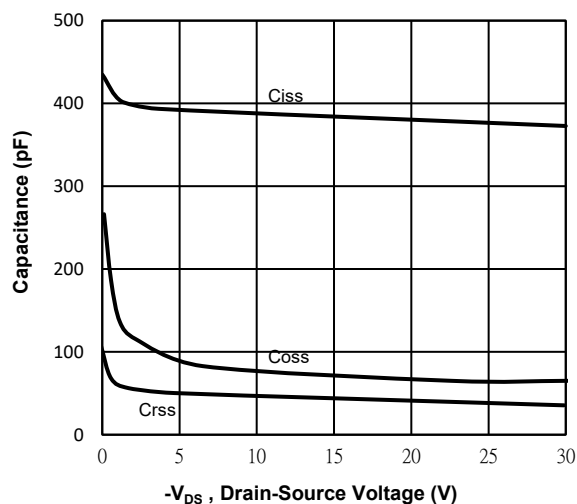
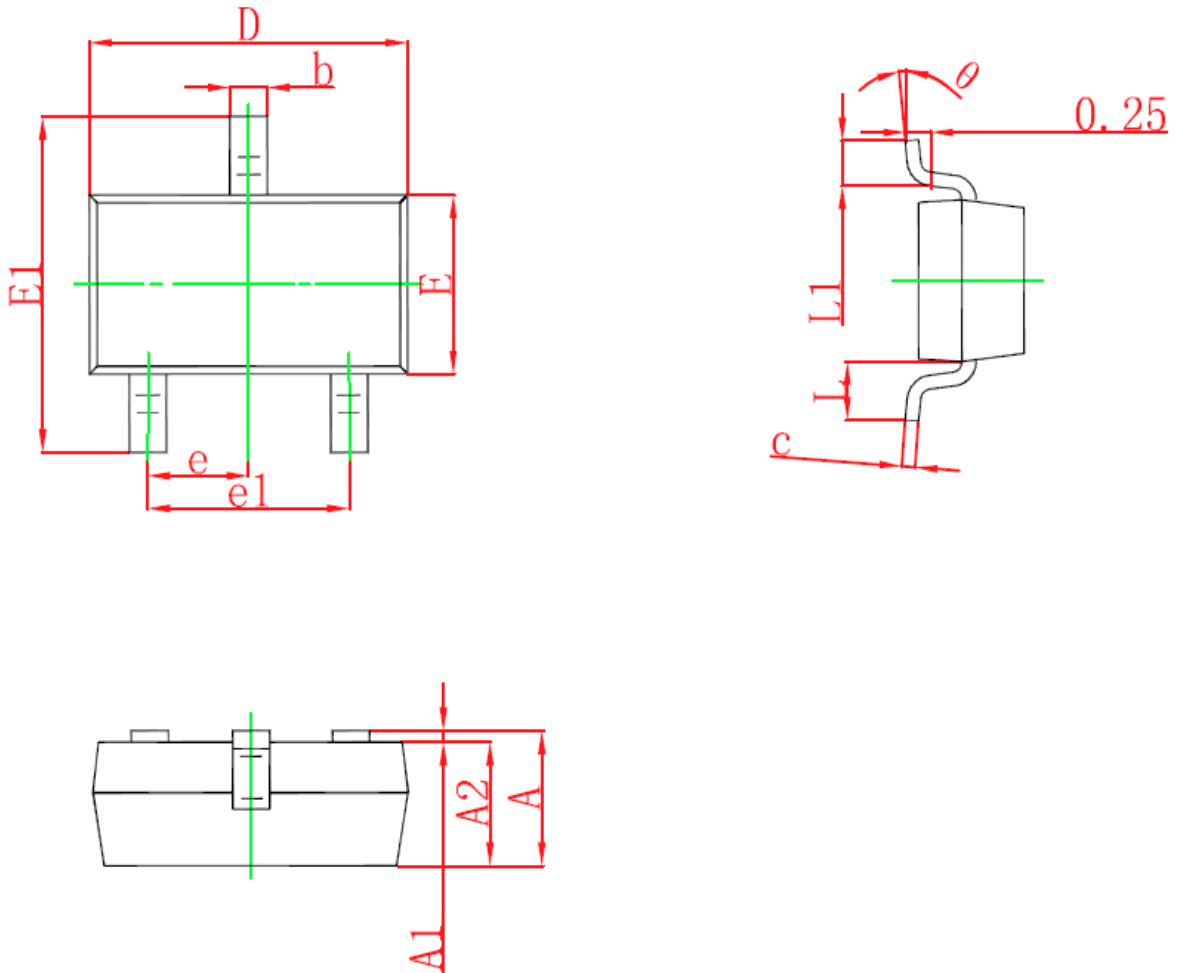


Fig6. Typical Capacitance Vs. Drain-Source

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°